The BaAl₄ structure and its derivatives from the R-Zn-Ga systems

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Abstract. Seven new ternary $RZn_{1+x}Ga_{3-x}$ (R = Ce, Pr, Nd, Sm, Ho and Er) and $Ce_5Zn_2Ga_{17}$ phases are synthesized for the first time. Their crystal structures are solved on basis of X-ray powder diffraction data. The above mentioned compounds belong to the BaAl₄ (space group *I*4/*mm*) and Rb₅Hg₁₉ (space group *I*4/*m*) structure types. Details of the structure of the Ce₅Zn₂Ga₁₇ compound and relationship with RZn_{2-x}Ga_{2+x} (BaAl₄ type) and R₃Zn_{8-x}Ga_{3+x} (La₃Al₁₁ type) are briefly discussed.

Introduction

The rare earths-transition metal-gallium systems have been intensively investigated in recent years with respect to their phase relations, crystal structures and magnetic and transport properties [1-4]. However, among them, the R-Zn-Ga systems were poorly studied: the phase diagram, crystal structure and physical properties of the compounds from the Yb-Zn-Ga system were reported in [5-7]; structural and magnetic studies on the RZn_{2-x}Ga_{2+x} (R = La, Ce, Pr, Nd, Sm, Eu, Gd, Yb) phases, with BaAl₄ and/or CaCu_{0.15}Ga_{3.85} structure types, can be found in [8-11]; identification of the new intermediate phases with the CeCu₂, CaIn₂, CeCd₂ and AlB₂ structure types from the RGa₂-RZn₂ (R = Y, La, Ce, Pr, Sm, Eu, Gd, Dy, Er, Tm) cross-section are published in [12,13]; structural studies on the new representatives with BaAl₄ (RZn_{2-x}Ga_{2+x}, R = Y, Gd, Tb, Dy), La₃Al₁₁ (R₃Zn_{8-x}Ga_{3+x}, R = Dy, Ho, Er, Tm, Lu) and BaHg₁₁ (RZn_{9-x}Ga_{2+x}, R = Y, Gd, Tb, Dy, Ho, Er, Tm) structure types are given in [14,15]; investigations on the YZn_xGa_{1-x} alloys are reported in [16]; single crystal studies of the defected La_{5-x}Zn_{1.5}Ga_{1.5} phase with W₅Si₃ are shown in [17]. Herein, we present data on the crystal structure of other new ternary phases from the R-Zn-Ga systems.

Experimental details

Metals with nominal purities > 99.95 wt. % (rare earth ingots, Zn spheres and Ga pieces) were used as starting materials. The samples, with a total weight 0.5-1.0 g, were prepared by heating the elements under vacuum at T > 900°C inside quartz ampoules, followed by annealing at 400°C for 1-3 months and quenched by submerging the quartz tubes into cold water.

X-ray phase and structural analysis were performed using a PANalitical X'Pert Pro diffractometer (Cu K α -radiation). The scans were taken in the $\theta/2\theta$ mode with the following parameters: 2θ region 15-120°; step scan 0.03°; counting time per step 15-20 s. The lattice parameters were obtained by least-squares fitting using the Latcon program [18]. The FullProf [19] program was used for Rietveld refinements. Pseudo-Voigt profile shape function was used. The background was refined with a polynomial function.

Results and discussion

Six new ternary phases, with BaAl₄ structure type, were identified in the annealed alloys with the CeZnGa₃, RZn_{1.5}Ga_{2.5} (R = Ce, Pr, Nd, Sm and Ho) and ErZn_{1.75}Ga_{2.25} compositions. Their calculated lattice parameters, as well as atom coordinates and thermal parameters are given in Table 1. The formation of R₃Zn_{8-x}Ga_{3+x} (0.5 < x < 4) phases with La₃Al₁₁ structure type was also confirmed in the annealed alloys. As examples, X-ray diffractograms of SmZn_{1.5}Ga_{2.5} and Er₃Zn₄Ga₇ are shown in Fig. 1*a* and 1*b*, respectively. The relation between the structures of R-Zn-Ga phases with BaAl₄ and La₃Al₁₁ structure types was discussed in [14,15].

Table 1. Crystanographic data for $NZh_{2-x}Oa_{2+x}$ phases (DaA14-type structure, 14/mini, $Z = 2$)								
Phase	CeZn _{1.5} Ga _{2.5}	$PrZn_{1.5}Ga_{2.5}$	NdZn _{1.5} Ga _{2.5}	SmZn _{1.5} Ga _{2.5}	HoZn _{1.5} Ga _{2.5}	ErZn _{1.75} Ga _{2.25}		
Lattice paramet	ters:							
a (Å)	4.2758(1)	4.2421(2)	4.2171(1)	4.1764(1)	4.0973(3)	4.0817(2)		
<i>c</i> (Å)	10.6680(3)	10.6865(5)	10.7134(3)	10.7534(3)	10.8177(9)	10.8443(5)		
$V(\text{\AA}^3)$	195.03(1)	192.31(1)	190.52(1)	187.56(1)	181.61(3)	180.72(2)		
Reliability factors:								
$R_{\rm B}, R_{\rm F}$ (%)	5.28, 4.44	6.03, 3.57	5.85, 4.63	7.70, 5.27	7.20, 4.53	7.38, 5.89		
$R_{\rm p}, R_{\rm wp}$ (%)	8.84, 11.6	10.7, 13.9	9.71, 12.7	10.2, 13.5	14.0, 18.0	11.8, 15.9		
Atom coordinates and thermal parameters:								
R (0 0 0),	1Ce	1Pr	1Nd	1Sm	1Ho	1Er		
$B_{\rm iso}({\rm \AA}^2)$	1.12(4)	0.92(4)	0.95(3)	0.94(4)	1.30(15)	0.98(6)		
M1(0 $\frac{1}{2}$ $\frac{1}{4}$),	1M	1M	1M	1M	1M	1M		
$B_{\rm iso}({\rm \AA}^2)$	1.16(5)	1.52(6)	1.38(5)	1.26(5)	1.52(16)	0.89(7)		
M2 (0 0 <i>z</i>),	1M	1M	1M	1M	1M	1M		
$B_{\rm iso}({\rm \AA}^2)$	0.38483(15)	0.38578(17)	0.38624(15)	0.38635(18)	0.3889(4)	0.3906(3)		
	0.84(5)	0.84(5)	0.84(4)	0.90(5)	0.90(11)	1.17(8)		
Mixture M	3/8Zn+5/8Ga	3/8Zn+5/8Ga	3/8Zn+5/8Ga	3/8Zn+5/8Ga	3/8Zn+5/8Ga	7/16Zn+9/16Ga		



Fig.1 X-ray diffraction patterns of $SmZn_{1.5}Ga_{2.5}(a)$, $Er_3Zn_4Ga_7(b)$ and $Ce_5Zn_2Ga_{1.7}(c)$.

X-ray analysis of ~Ce₂₀Zn₁₀Ga₇₀ as-prepared alloys at 1000°C indicated the existence of a new compound and monophasic samples were obtained for the Ce_{20.8}Zn_{8.4}Ga_{70.8} (Ce₅Zn₂Ga₁₇) composition. XRD data was successfully indexed within a tetragonal unit cell, and taking into account stoichiometry, symmetry and two possible space groups (I4/m or $I\overline{4}$), the Rb₅Hg₁₉ structure type was chosen as a model for the crystal structure refinement. Results of such refinement can be seen in Fig. 1c. Atoms parameters as well as interatomic distances are given in Tables 2 and 3. The shortest interatomic distances are in the good agreement with the sum of the atomic radii of pure metals. Due to the small difference between Zn and Ga scattering factors, statistical mixture of these elements was presented as M = 0.10Zn + 0.90Ga. Ce atoms occupy the Rb sites, while small atoms M (Zn and Ga) are distributed over the Hg positions. It should be noted that the final XRD refinement indicates a partial occupation of the 2a, 4d and 16i Wyckoff positions. Similar tendency was also observed for other gallides, $R_5Ag_{2-x}Ga_{17-y}$ (R = Gd, Tb), with Rb₅Hg₁₉ structure type [20].

		-					
Atom	Site	x	у	Ζ	$B_{\rm iso}({\rm \AA}^2)$	Occ.	
Cel	2b	0	0	1/2	1.0(2)	1Ce	
Ce2	8 <i>h</i>	0.3074(3)	0.1057(4)	0	0.9(1)	1Ce	
M1	2 <i>a</i>	0	0	0	0.9(4)	0.78M	
M2	4 <i>d</i>	0	1/2	1/4	0.8(3)	0.91M	
M3	16 <i>i</i>	0.2053(6)	0.3963(7)	0.1248(3)	0.9(1)	0.94M	
M4	16 <i>i</i>	0.0869(5)	0.1788(4)	0.2297(4)	0.8(1)	1M	
$R_{\rm B} = 8.54\%$, $R_{\rm F} = 6.48\%$, $R_{\rm p} = 10.3\%$, M = 0.10Zn + 0.90Ga							

Table 2 Interstance distances and econdination number of the stamp in the Co Zn Ca

Table 2. Atom coordinates and isotropic displacement parameters of Ce₅Zn₂Ga₁₇ (Rb₅Hg₁₉-type structure, *I*4/*m*, *Z* = 2), with lattice parameters *a* = 9.7240(2) Å, *c* = 10.1108(3) Å, *V* = 956.03(4) Å³.

В		/	P	·

A toms $d(\hat{\lambda})/CN$ A toms $d(\hat{\lambda})/CN$ A toms $d(\hat{\lambda})/CN$					
Atoms	u(A)/CN	Atoms	u(A)/CN	Atoms	u(A)/CN
Ce1-	16	M2-	8	M1-	12
-8M3	3.290(6)	-4M3	2.570(5)	-8M4	3.022(4)
-8M4	3.348(4)	-4Ce2	3.310(2)	-4Ce2	3.161(3)
Ce2-	13	M3-	9	M4-	9
-1M1	3.161(3)	-1M3	2.524(4)	-1M3	2.604(7)
-2M4	3.235(5)	-1M2	2.570(5)	-1M3	2.621(7)
-2M4	3.240(5)	-1M4	2.604(7)	-1M3	2.631(7)
-2M3	3.250(7)	-1M4	2.621(7)	-2M4	2.734(6)
-2M3	3.291(7)	-1M4	2.631(7)	-1M1	3.022(4)
-2M2	3.310(2)	-1Ce2	3.250(7)	-1Ce2	3.235(5)
-2M3	3.389(7)	-1Ce1	3.290(6)	-1Ce2	3.240(5)
		-1Ce2	3.291(7)	-1Ce1	3.348(4)
		-1Ce2	3.389(7)		

Projection of the Ce₅Zn₂Ga₁₇ structure on the *XY* plane is shown in the top of Fig. 2*a*. Unit cell is marked by bold dark lines. This phase can be seen as an intergrown structure of the two types of internal and/or external deformed BaAl₄-like unit cells (slabs) along *z* axis. Here, the tetragonal BaAl₄ subcells with $a_0 = 4.267$ Å and $c_0 = 10.111$ Å are shown by dotted squares. Calculated " a_0 " of deformed BaAl₄ subcell vary between 4.273 and 4.267 Å. The sharp angle ∠Ce2 is equal to 87.3°. Similar to the RZn_{2-x}Ga_{2-x} phases with BaAl₄ type, the small M (Zn and Ga) atoms form a three-dimensional network in the structure of Ce₅Zn₂Ga₁₇. Part of these nets is shown in the centre and bottom part of Fig. 2*a*. Surroundings of the Ce and M (Zn and Ga) atoms are also similar to the BaAl₄ type phases.

Fig. 2*b* shows the relationship between the BaAl₄, La₃Al₁₁ and Rb₅Hg₁₉ structures of the R-Zn-Ga phases. The last two structures can be interpreted as a defected variant of the BaAl₄ structure type, where the collapsing of part of the small atoms is observed. The general formula A_nB_{4n-m} can be used to describe such structures, with *n* - number of the BaAl₄ subcell (with lattice constants a_0 and c_0) and *m* - pair of collapsing atoms (2 \rightarrow 1). Transformations of above mentioned structure are following: (LaAl₄)₃ = La₃Al₁₂ \rightarrow La₃Al₁₁ (*n* = 3, *m* = 1; *a* ~ *a*₀, *b* ~ *c*₀, *c* ~ 3*a*₀) and (RbHg₄)₅ = Rb₅Hg₂₀ \rightarrow Rb₅Hg₁₉ (*n* = 5, *m* = 1; *a* ~ $\sqrt{5a_0}$, *c* ~ *c*₀). A more detailed description of the Rb₅Hg₁₉ type can be found in [21].



Fig. 2 Projection of Ce₅Zn₂Ga₁₇ on *XY* plane and three-dimensional [ZnGa] network (*a*) (dark filled circles represent Ce atoms; Zn and Ga atoms are represented by white balls). Relationship between BaAl₄, La₃Al₁₁ and Rb₅Hg₁₉ structure types (*b*).

Conclusions

Seven new phases, namely, $RZn_{1+x}Ga_{3-x}$ (R = Ce, Pr, Nd, Sm, Ho and Er) and $Ce_5Zn_2Ga_{17}$, were identified by means of X-ray diffraction. They belong to the known structure types BaAl₄ and Rb₅Hg₁₉, respectively. Crystal structures of the title compounds were fully investigated. The coordination of the atoms, interatomic distances and relation with other structures of the Ce₅Zn₂Ga₁₇ compound were discussed. The available data on the R-M-X (R - rare earth, M - Zn and Cd, X - Al and Ga) systems point to the possibility of existence of new compounds of the above cited structure types in the yet unexplored systems.

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